

## MOSFET N-KANAL POWER MOS

Manufacturers	<a href="#">Infineon Technologies Corporation</a>
Package/Case	TO-220
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for IPP045N10N3G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

IPP045N10N3G is a power MOSFET (Metal Oxide Semiconductor Field Effect Transistor) manufactured by Infineon Technologies. It is designed for use in various power switching applications where high efficiency and reliability are required.

### Features

- Drain-source voltage (V<sub>ds</sub>) rating of 100V
- Continuous drain current (I<sub>d</sub>) rating of 45A
- Low on-state resistance (R<sub>ds(on)</sub>) of 4.5mΩ
- Fast switching speed
- Low gate charge
- Avalanche energy specified

### Application

- DC-DC converters
- Power supplies
- Motor drives
- Inverters
- Solar inverters
- Uninterruptible power supplies (UPS)
- Battery management systems (BMS)



## Related Products



### [IPP60R070CFD7](#)

Infineon Technologies Corporation  
TO-220-3



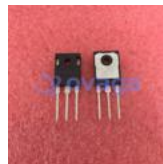
### [IPB180N06S4-H1](#)

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### [IPG20N04S4-12](#)

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### [IPW65R080CFD](#)

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[IPD25N06S4L-30](#)

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[IPD180N10N3G](#)

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